

# ZXMHN6A07T8

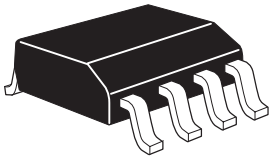
## 60V N-CHANNEL MOSFET H-BRIDGE

### SUMMARY

$V_{(BR)DSS} = 60V$  ;  $R_{DS(on)} = 0.3\Omega$ ;  $I_D = 1.6A$

### DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



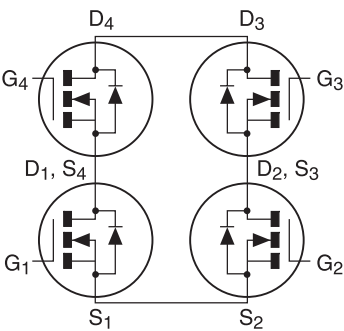
SM8

### FEATURES

- Compact package
- Low on state losses
- Low drive requirements
- Operates up to 60V
- 1 Amp continuous rating

### APPLICATIONS

- Motor control



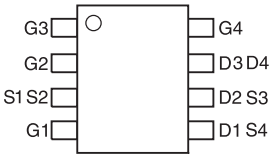
### ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMHN6A07T8TA	7"	12mm	1,000 units
ZXMHN6A07T8TC	13"	12mm	4,000 units

### DEVICE MARKING

- ZXMH  
N6A07

### PINOUT



TOP VIEW

# ZXMHN6A07T8

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DSS}$	60	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current ( $V_{GS} = 10V$ ; $T_A = 25^\circ C$ ) <sup>(b) (d)</sup>	$I_D$	1.6	A
( $V_{GS} = 10V$ ; $T_A = 70^\circ C$ ) <sup>(b) (d)</sup>		1.3	A
( $V_{GS} = 10V$ ; $T_A = 25^\circ C$ ) <sup>(a) (d)</sup>		1.4	A
Pulsed drain current <sup>(c)</sup>	$I_{DM}$	9	A
Continuous source current (body diode) <sup>(b) (d)</sup>	$I_S$	1	A
Pulsed source current (body diode) <sup>(c)</sup>	$I_{SM}$	9	A
Total power dissipation at $T_A = 25^\circ C$	$P_{TOT}$		
Any Single transistor "on" <sup>(a) (d)</sup>		1.1	W
Single transistor 'on' <sup>(b) (d)</sup>		1.4	W
Two transistors 'on' equally <sup>(a) (e)</sup>		1.6	W
Linear derating factor above $25^\circ C$ <sup>(a)</sup>			
Single transistor "on" <sup>(a) (d)</sup>		8.8	mW/ $^\circ C$
Single transistor 'on' <sup>(b) (d)</sup>		11.2	mW/ $^\circ C$
Two transistors 'on' equally <sup>(a) (e)</sup>		13.2	mW/ $^\circ C$
Thermal resistance - junction to ambient	$R_{th(j-amb)}$		
Single transistor "on" <sup>(a) (d)</sup>		114	$^\circ C/W$
Single transistor "on" <sup>(b) (d)</sup>		89	$^\circ C/W$
Two transistors 'on' equally <sup>(a) (e)</sup>		76	$^\circ C/W$
Operating and storage temperature range	$T_j, T_{stg}$	-55 to + 150	$^\circ C$

(a) For a device mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2oz weight copper in still air conditions with the heat sink split into three equal areas, one for each drain connection.

(b) For a device surface mounted on a FR4 PCB at  $t \leq 10$  sec.

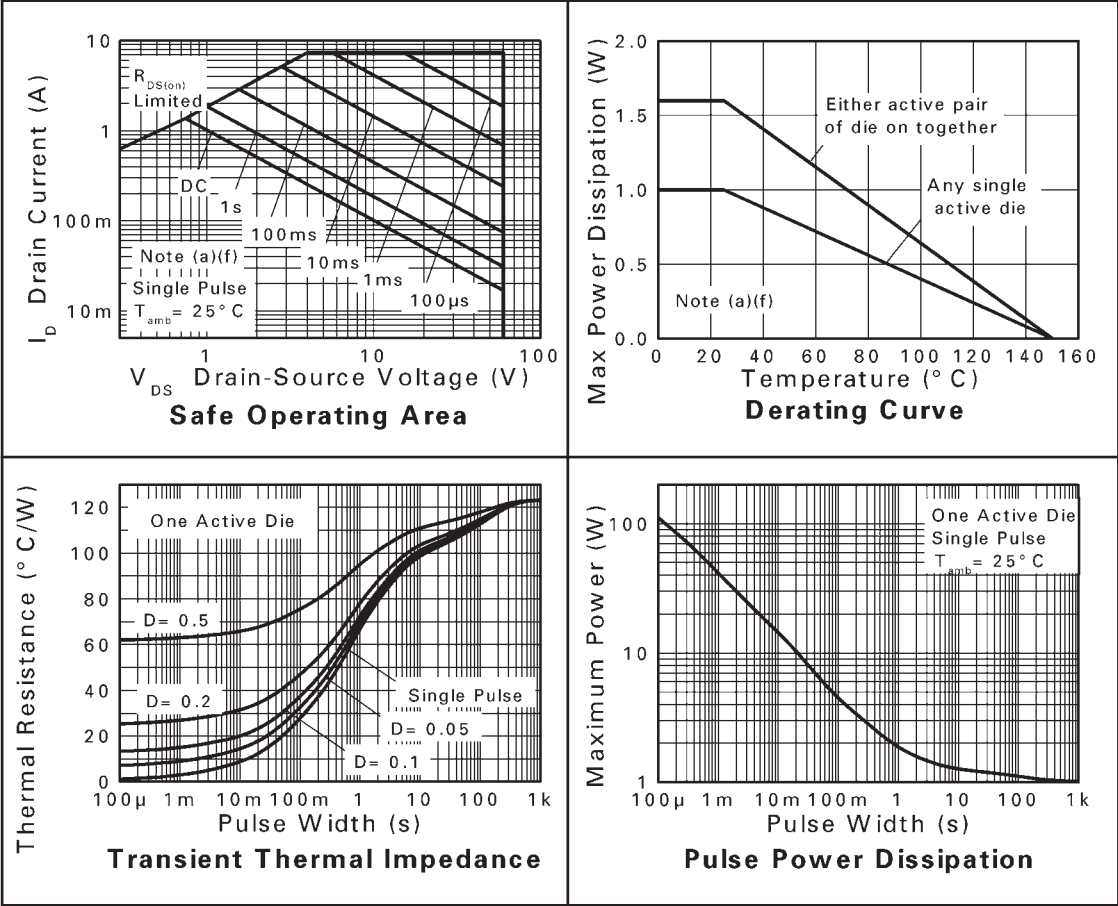
(c) Repetitive rating on 50mm x 50mm x 1.6mm FR4 PCB, duty cycle 2%, pulse width 300 $\mu$ S in still air conditions with the heat sink split into three equal areas, one for each drain connection.

(d) For device with one active die.

(e) For any two die not sharing the same drain connection.

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CHARACTERISTICS



# ZXMHN6A07T8

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

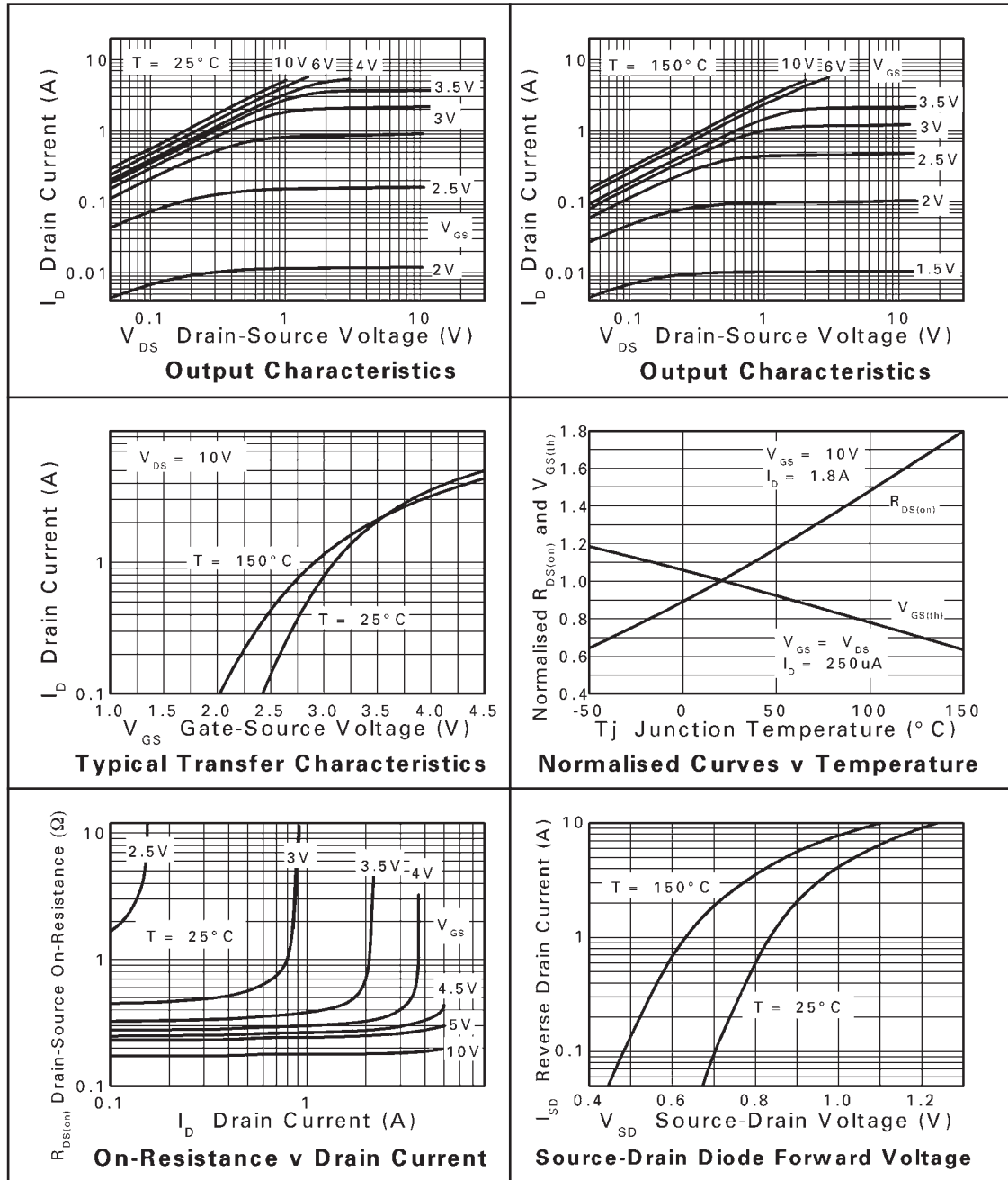
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-source breakdown voltage	$V_{(BR)DSS}$	60			V	$I_D = 250\mu A$ , $V_{GS} = 0V$
Zero gate voltage drain current	$I_{DSS}$			1.0	$\mu A$	$V_{DS} = 60V$ , $V_{GS} = 0V$
Gate-body leakage	$I_{GSS}$			100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
Gate-source threshold voltage	$V_{GS(th)}$	1.0		3.0	V	$I_D = 250\mu A$ , $V_{DS} = V_{GS}$
Static drain-source on-state resistance <sup>(1)</sup>	$R_{DS(on)}$			0.3 0.45	$\Omega$ $\Omega$	$V_{GS} = 10V$ , $I_D = 1.8A$ $V_{GS} = 4.5V$ , $I_D = 1.3A$
Forward transconductance <sup>(1) (3)</sup>	$g_{fs}$		2.3		S	$V_{DS} = 15V$ , $I_D = 1.8A$
DYNAMIC <sup>(3)</sup>						
Input capacitance	$C_{iss}$		166		pF	$V_{DS} = 40V$ , $V_{GS} = 0V$ $f = 1MHz$
Output capacitance	$C_{oss}$		20		pF	
Reverse transfer capacitance	$C_{rss}$		9		pF	
SWITCHING <sup>(2) (3)</sup>						
Turn-on-delay time	$t_{d(on)}$		1.8		ns	$V_{DD} = 30V$ , $I_D = 1.8A$ $R_G \cong 6.0\Omega$ , $V_{GS} = 10V$
Rise time	$t_r$		1.4		ns	
Turn-off delay time	$t_{d(off)}$		4.9		ns	
Fall time	$t_f$		2.0		ns	
Total gate charge	$Q_g$		3.2		nC	$V_{DS} = 30V$ , $V_{GS} = 10V$ $I_D = 1.8A$
Gate-source charge	$Q_{gs}$		0.7		nC	
Gate drain charge	$Q_{gd}$		0.8		nC	
SOURCE-DRAIN DIODE						
Diode forward voltage <sup>(1)</sup>	$V_{SD}$			0.95	V	$T_J = 25^\circ C$ , $I_S = 0.45A$ , $V_{GS} = 0V$
Reverse recovery time <sup>(3)</sup>	$t_{rr}$		21		ns	$T_J = 25^\circ C$ , $I_F = 1.0A$ ,
Reverse recovery charge <sup>(3)</sup>	$Q_{rr}$		21		nC	$di/dt = 100A/\mu s$

### NOTES

- (1) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .  
(2) Switching characteristics are independent of operating junction temperature.  
(3) For design aid only, not subject to production testing.

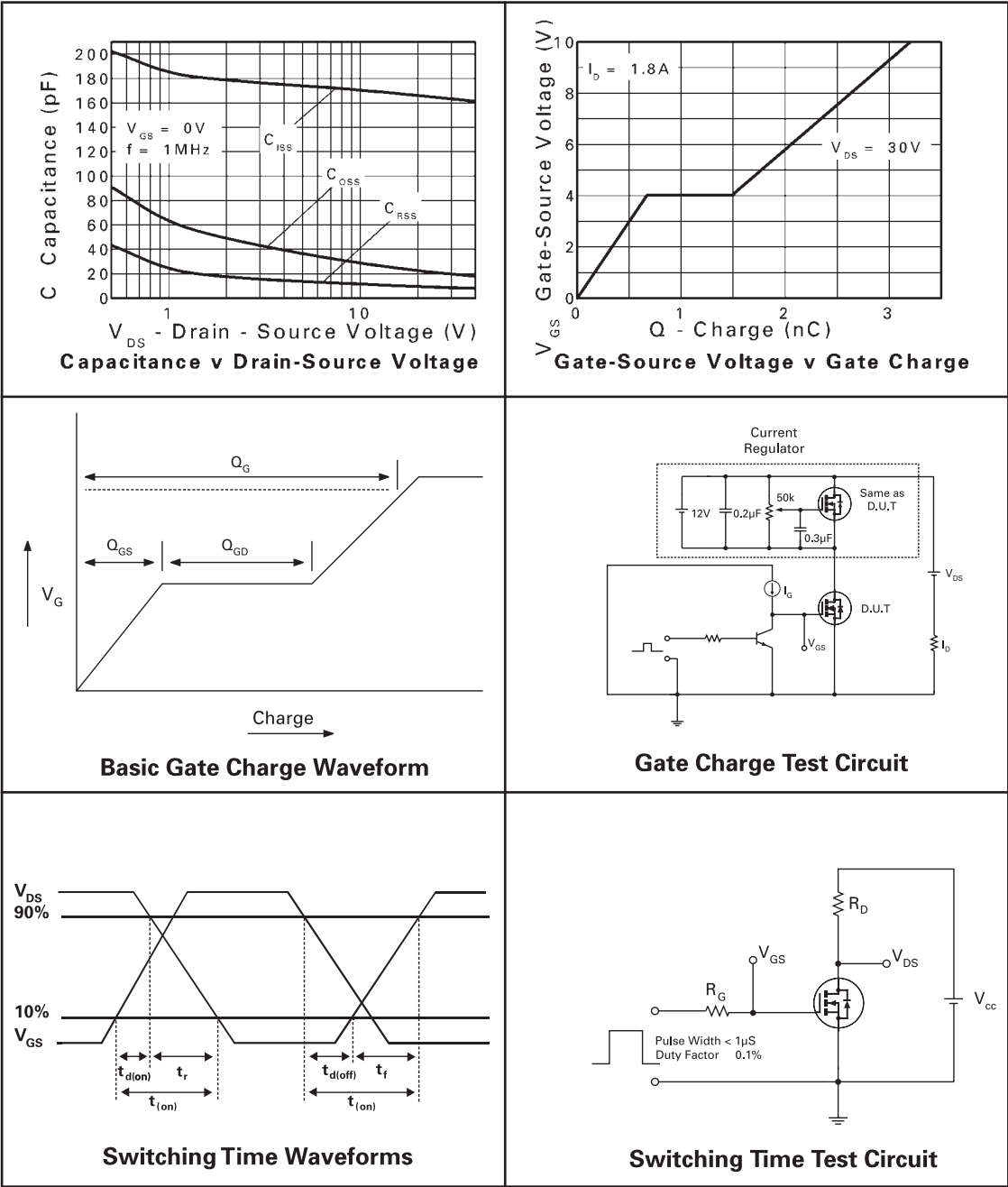
# ZXMHN6A07T8

## TYPICAL CHARACTERISTICS



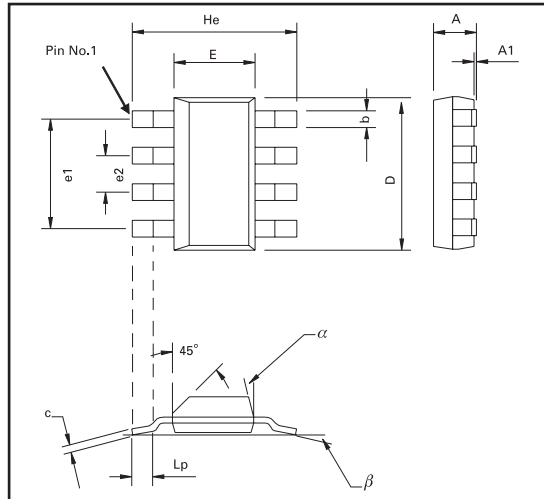
ZXMHN6A07T8

TYPICAL CHARACTERISTICS



# ZXMHN6A07T8

## PACKAGE OUTLINE



Controlling dimensions are in millimeters. Approximate conversions are given in inches

## PACKAGE DIMENSIONS

DIM	Millimeters			Inches			DIM	Millimeters			Inches		
	Min	Max	Typ.	Min	Max	Typ.		Min	Max	Typ.	Min	Max	Typ.
A	-	1.7	-	-	0.067	-	e1	-	-	4.59	-	-	0.1807
A1	0.02	0.1	-	0.008	0.004	-	e2	-	-	1.53	-	-	0.0602
b	-	-	0.7	-	-	0.0275	He	6.7	7.3	-	0.264	0.287	-
c	0.24	0.32	-	0.009	0.013	-	Lp	0.9	-	-	0.035	-	-
D	6.3	6.7	-	0.248	0.264	-	$\alpha$	-	15°	-	-	15°	-
E	3.3	3.7	-	0.130	0.145	-	$\beta$	-	-	10°	-	-	10°

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